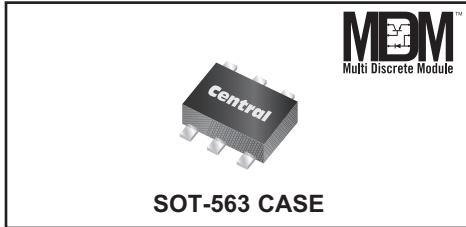


CMLM0575

**MULTI DISCRETE MODULE™  
SURFACE MOUNT SILICON  
N-CHANNEL MOSFET AND  
LOW V<sub>F</sub> SCHOTTKY DIODE**



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**APPLICATIONS:**

- DC-DC Converters
- Boost Converters
- Motor Drive Controls
- Battery Powered Portable Equipment

**MAXIMUM RATINGS - CASE: (T<sub>A</sub>=25°C)**

Power Dissipation (Note 1)	
Power Dissipation (Note 2)	
Power Dissipation (Note 3)	
Operating and Storage Junction Temperature	
Thermal Resistance	

**MAXIMUM RATINGS - Q1: (T<sub>A</sub>=25°C)**

Drain-Source Voltage	
Gate-Source Voltage	
Continuous Drain Current	

**MAXIMUM RATINGS - D1: (T<sub>A</sub>=25°C)**

Peak Repetitive Reverse Voltage	
Continuous Forward Current	
Peak Repetitive Forward Current, tp≤1.0ms	
Peak Forward Surge Current, tp=8.0ms	

**ELECTRICAL CHARACTERISTICS - Q1: (T<sub>A</sub>=25°C unless otherwise noted)**

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>GSSF</sub> , I <sub>GSSR</sub>	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =0			1.0	μA
I <sub>DSS</sub>	V <sub>DS</sub> =16V, V <sub>GS</sub> =0			100	nA
BV <sub>DSS</sub>	V <sub>GS</sub> =0, I <sub>D</sub> =250μA	20			V
V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.5		1.1	V
V <sub>SD</sub>	V <sub>GS</sub> =0, I <sub>S</sub> =200mA			1.1	V
r <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =600mA		0.14	0.23	Ω
r <sub>DS(ON)</sub>	V <sub>GS</sub> =2.5V, I <sub>D</sub> =500mA		0.2	0.275	Ω
r <sub>DS(ON)</sub>	V <sub>GS</sub> =1.8V, I <sub>D</sub> =350mA			0.7	Ω

- Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0mm<sup>2</sup>  
 (2) FR-4 Epoxy PC Board with copper mounting pad area of 4.0mm<sup>2</sup>  
 (3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4mm<sup>2</sup>

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMLM0575 is a Multi Discrete Module™ consisting of a single N-Channel enhancement-mode MOSFET and a low V<sub>F</sub> Schottky diode packaged in a space saving SOT-563 surface mount case. This device is designed for small signal general purpose applications where size and operational efficiency are prime requirements.

**MARKING CODE: 75C**

**FEATURES:**

- High Current MOSFET (I<sub>D</sub>=650mA)
- ESD protection up to 2kV
- Low r<sub>DS(ON)</sub> MOSFET (275mΩ MAX @ V<sub>GS</sub>=2.5V)
- Low V<sub>F</sub> Schottky Diode (0.47V MAX @ 0.5A)

**SYMBOL**

P <sub>D</sub>	350	mW
P <sub>D</sub>	300	mW
P <sub>D</sub>	150	mW
T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
θ <sub>JA</sub>	357	°C/W

**SYMBOL**

V <sub>DS</sub>	20	V
V <sub>GS</sub>	8.0	V
I <sub>D</sub>	650	mA

**SYMBOL**

V <sub>R</sub> RM	40	V
I <sub>F</sub>	500	mA
I <sub>FRM</sub>	3.5	A
I <sub>FSM</sub>	10	A

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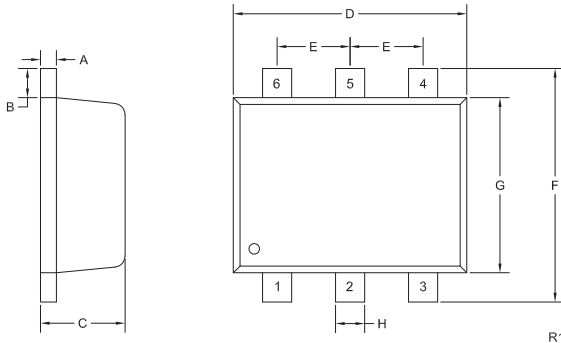
**ELECTRICAL CHARACTERISTICS - Q1 Continued:** (T<sub>A</sub>=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Q <sub>g(tot)</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =500mA		1.58		nC
Q <sub>gs</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =500mA		0.17		nC
Q <sub>gd</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =500mA		0.24		nC
g <sub>FS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =100mA	200			mS
C <sub>rss</sub>	V <sub>DS</sub> =16V, V <sub>GS</sub> =0, f=1.0MHz		18		pF
C <sub>iss</sub>	V <sub>DS</sub> =16V, V <sub>GS</sub> =0, f=1.0MHz		100		pF
C <sub>oss</sub>	V <sub>DS</sub> =16V, V <sub>GS</sub> =0, f=1.0MHz		16		pF
t <sub>on</sub>	V <sub>DD</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =200mA, R <sub>G</sub> =10Ω		10		ns
t <sub>off</sub>	V <sub>DD</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =200mA, R <sub>G</sub> =10Ω		25		ns

**ELECTRICAL CHARACTERISTICS - D1:** (T<sub>A</sub>=25°C)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>R</sub>	V <sub>R</sub> =10V			20	μA
I <sub>R</sub>	V <sub>R</sub> =30V			100	μA
BV <sub>R</sub>	I <sub>R</sub> =500μA	40			V
V <sub>F</sub>	I <sub>F</sub> =100μA			0.13	V
V <sub>F</sub>	I <sub>F</sub> =1.0mA			0.21	V
V <sub>F</sub>	I <sub>F</sub> =10mA			0.27	V
V <sub>F</sub>	I <sub>F</sub> =100mA			0.35	V
V <sub>F</sub>	I <sub>F</sub> =500mA			0.47	V
C <sub>J</sub>	V <sub>R</sub> =1.0V, f=1.0MHz			50	pF

**SOT-563 CASE - MECHANICAL OUTLINE**



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.0027	0.007	0.07	0.18
B	0.008		0.20	
C	0.017	0.024	0.45	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.045	0.049	1.15	1.25
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R1)

**LEAD CODE:**

- 1) Gate Q1
- 2) Source Q1
- 3) Cathode D1
- 4) Anode D1
- 5) Anode D1
- 6) Drain Q1

**MARKING CODE: 75C**

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